

Efficacy and Cost Advantages are Driving Ion Implant Adoption in Commercial PV Cell Fabrication

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POWERING INNOVATION, DELIVERING VALUE.

COMPANY CONFIDENTIAL 7/14/16

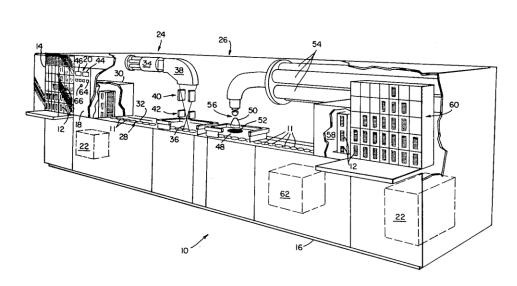
Outline

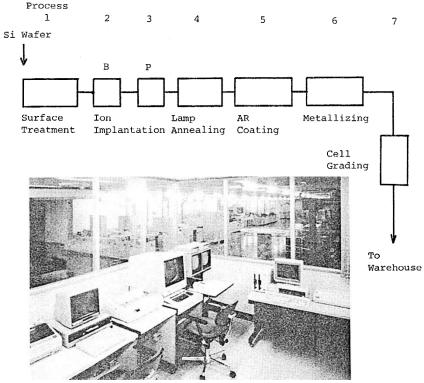


- PV Implant Brief History Crossing the Chasm
- PV market
 - Cost and Cell Efficiency
- Intevac Implant system at 3000 wph
 - How it works?
 - Benefits to customers
 - Cell results
- Patterning capability for advanced devices

1980's Integrated Implant Solar Solutions







1982 - An integrated system: implant, e-beam annealer under common vacuum system with no wet chemistry for front contact cells

Armini and Little, Spire Corp (USA), patent 4,353,160 "Solar cell Junction processing system"

1985 - Hoxan Corp (Japan) Bifacial cell 4" wafers, 9MW with 11% efficiency

Y, Tahara et. al., "High Throughput Automated Junction Formation by Ion Implantation and Halogen Lamp Anneal For 9MW Production" IEEE 1985 (4" wafers)

Ion Implant in Solar PV: Recent History 2008+

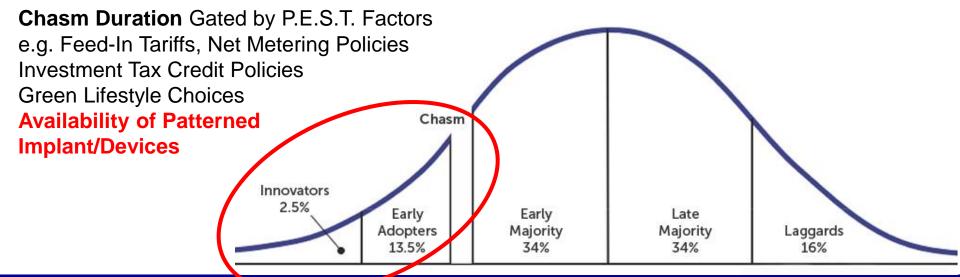


"As of the end of August [2011], **over ten PV manufacturers** in the US, China, Taiwan, South Korea and Europe have received [Varian] Solion systems." (Source: <u>Varian</u>)

"Amtech to sell majority stake in ion implant subsidiary Kingstone Technology." (Source: PV Tech, 24 July 2015)

"Applied Materials Withdraws from Solar Ion Implant." (Source: PV Tech, 19 Aug 2015)

~100 Total PV Cell Manufacturers; Chasm Theory Suggests ~16 Total Innovators / Early Adopters in this Population



PV Market Growth, Players and Flavors



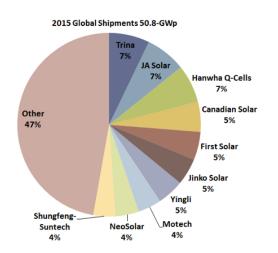


Fast Growth: 66 GW → 95 GW in 2020

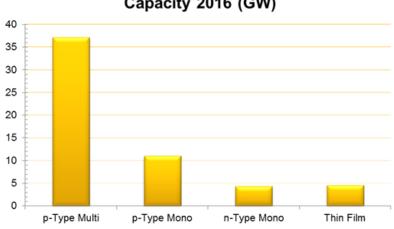
100 PV manufacturers → ~11.7B cells/year

• p-type Multi→ p and n Mono transition

Source: Greentech Media 02 May 2016



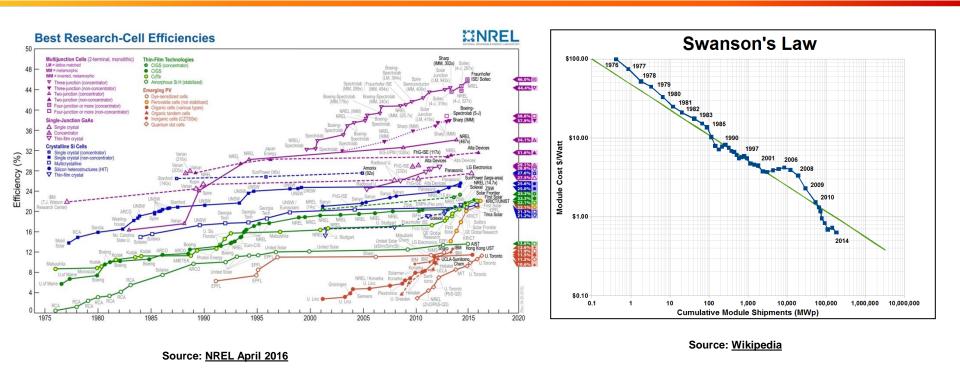
W-W Installed PV Cell Manufacturing Capacity 2016 (GW)



Source: Paula Mints 08 April 2016
Source: Solar Media March 2016

PV Cell Efficiencies and Cost Demands



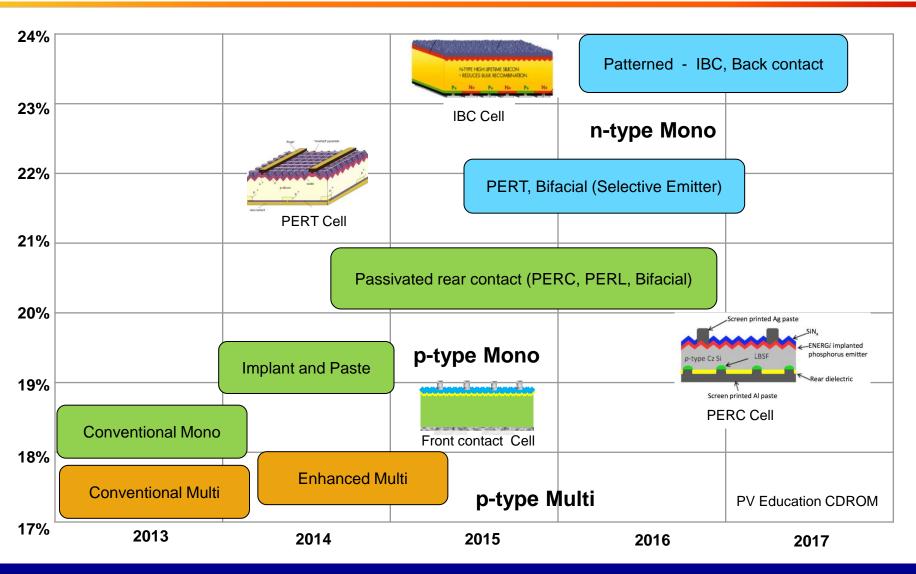


SWANSON LAW:
Cell cost falls by 20% with each doubling of manufacturing

△ 0.1% Efficiency Makes Headlines and Tenths of Pennies Count Cost of solar module now <\$1 per Watt

c-Si Solar Cell Roadmap: Efficiency is King





c-Si Solar Cell Roadmap: Cost is also King



Ion Implant Process Flow Advantage

Cell Type	Diffusion Ion Implant	
	process steps	process steps
Front Contact	3	2
Front Contact (with Ox)	4	2
Front Contact	5	2
Bi-Facial	6	2
IBC	~6	2

Texture
Implant
B emitter
Implant
P BSF
Co-anneal
Front
Al203
Al203
SiNx
Metal
contacts

Low cost of ownership Bi-Facial cell solution

Oxide growth

Patterned etch resist

Wet etch Si02

Boron Diffusion

Patterned etch resist

Wet etch Si02

Remove resist & clean

POCI3 diffusion

Rear etch resist

Etch front Si02

Textile front

Remove rear resist & clean

POCI3 diffusion

Front SiNx

Front SiNx

IBC by multiple diffusion masks and furnace diffusions

Front n FSF implant
Rear patterned n implant
Rear patterned n implant
Furnace anneal
Front SiNx

IBC by patterned implant

Intevac Equipment Products



200 Lean[®] PVD System for Hard Disk





- Intevac is a leader in high productivity equipment
- Capabilities to address multiple advanced solar applications
- Focus on higher cell efficiency and lower cost / Watt

ENERGi[™] Ion Implant





ENERG*i*[™] - Implant System Specifically for Solar



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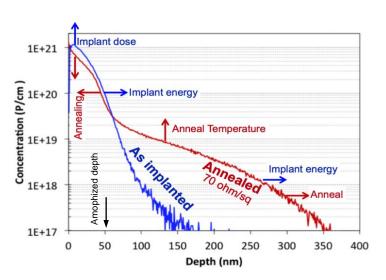
ENERG*i* Ion Implant System Fully automated

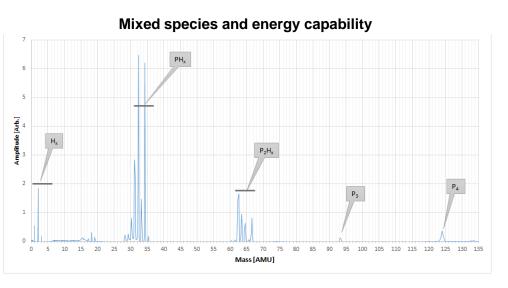
- Lower in cost than diffusion process flow
- Higher cell efficiency than diffusion flow
- Running millions of cells in full production
 - Highest throughput of 3000 wph
- Demonstrated advanced cell design
 - Front contact cell
 - PERC
 - N-PERT
 - Bifacial cell
 - IBC
 - Unique Patterning (Selective Emitter and IBC)
 Patent Pending

Non-Mass Analyzed Atomic Profile Advantages



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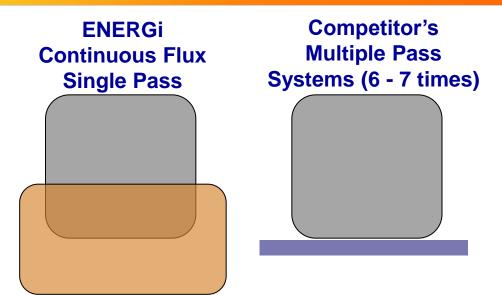


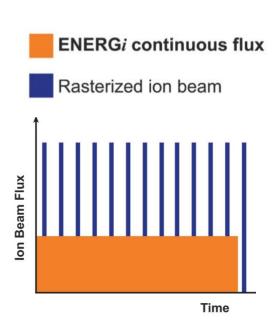


- Implant all precursor bi-products very near surface (Similar to Diffusion)
 - Annealing only impacts the diffused parts
- High dose rate → Full Amorphization:
 - Leading to complete anneal and activation Solid Phase Epitaxial Regrowth (SPER)
- Near surface profile tailoring is important to optimize cell parameters
 - For Ag pastes, optimize contact resistance vs Voc

ENERG*i*[™] Continuous Flux Implant





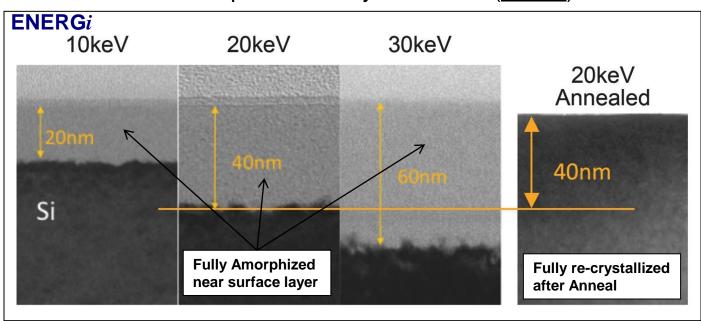


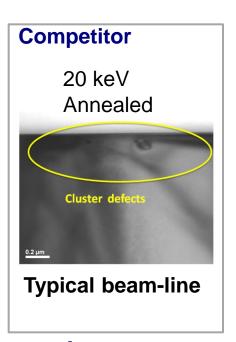
- Dynamic annealing occurs between passes (no beam)
- Single pass helps to fully amorphize and fully anneal

Near Surface Amorphization and Regrowth



- ENERGi generates fully amorphized near surface layer
 - Due to <u>high dose rate</u> and <u>single pass</u>
 - Good/complete amorphization is desired for best annealing
- This layer will fully re-crystallize during anneal
 - Solid Phase Epitaxial Recrystallization (SPER)





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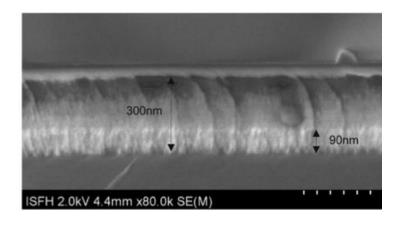
ENERGi ion implant enables high quality epitaxial regrowth

Boron Implant Advantages



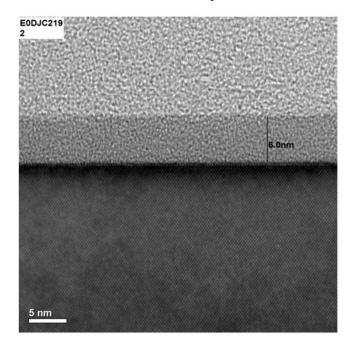
Diffusion

- Boron Rich Layer (BRL) impact minority carrier life time
- BSG removal is difficult
- More process steps
- **Higher CoO**



Ion Implant

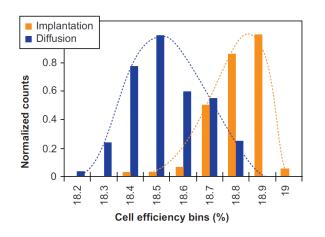
- No Boron rich layer or BSG
- Precise Boron dose and single sided doping
- Superior surface interface & emitter
- **Excellent uniformity and repeatability**
- Low cost of ownership

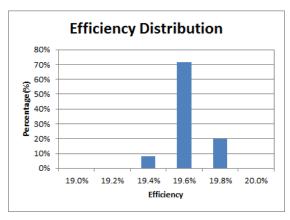


ENERG*i* in Production – Front Contact Cell



- Millions of cells processed (50+k wafer per day)
 - Higher Cell efficiencies and V_{oc} than diffusion
 - Narrow efficiency distribution

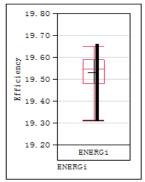


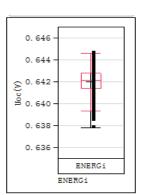


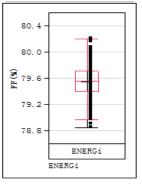
Narrow distribution → Module matching

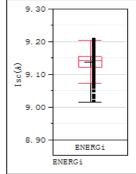
NCell	Uoc(V)	Isc(A)	FF(%)
19.95%	0.6461	9.3264	80.19

Champion data from customers









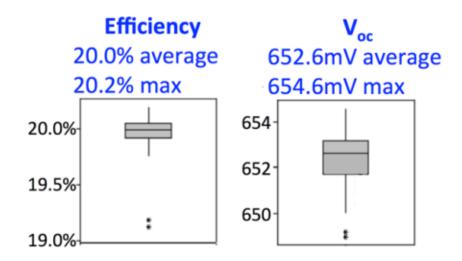
Industrial data from customers

Data shown with customer's permission

ENERG*i* in Production – PERC cells



- Rear passivated cells such as PERC are a challenge for diffusion
- Implant demonstrated good results (With oxy-nitride passivation only)
 - 0.4% gain over POCL3
 - 0.2% over competitor next generation system



Data shown with customer's permission

ENERGi Boron Data (N-PERT & Bifacial)



Low cost of ownership Bi-Facial cell solution

- ENERGi recipes developed for both N-PERT and Bi-facial
- ENERGi (P+ B) and Co-anneal simplifies flow and lowers cost of ownership

Rsheet B Emitter (Ω / □)	Rsheet P-BSF (Ω / □)	J _{OE} (fA/cm²)	MCL (0.1 sun) (µsecs)	Implied V _{oc} (mV)
88	56	65	131	650

N-type Si, 156mm 1.4 Ω -cm Cz, textured ENERGi Boron + ENERGi Phosphorous with Co-anneal Passivation B-Emitter Plasma ALD Al2O3, SiNx Passivation P-BSF, insitu thermal oxide + SiNx

Data shown with customer's permission

Ion Implant in Solar PV: Today

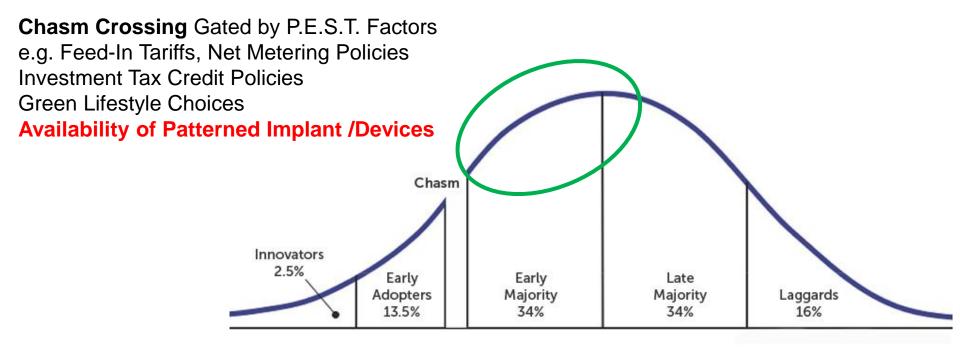


"Tool Order: Intevac to supply ion implant tool to solar cell producer."

(Source: PV Tech, 29 Sept 2015)

"Intevac wins ion implant systems orders from Chinese solar cell producer."

(Source: <u>PV Tech, 25 May 2016</u>)



ENERGi - Implant System Specifically for Solar



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ENERGi Ion Implant System Fully automated

- Lower in cost than diffusion emitter flow
- Higher cell efficiency than diffusion emitter flow
 - N-type doping front contact at 20+% efficiency
- Running millions of cells in full production
- Highest throughput of 3000 wph
- Demonstrated advanced cell design
 - Front contact
 - PERC
 - N-PFRT
 - Bifacial
 - IBC
 - Patented Unique patterning (Selective and IBC)



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